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HALOGEN

FREE

N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω) TYP.	I _D (A)	Q _g (TYP.)			
40	0.8 at V _{GS} = 10 V	320	245 nC			

TOLL Pin Configuration

N-Channel MOSFET

FEATURES

- DT-Trench Power MOSFET
- 100 % R_q and UIS tested

APPLICATIONS

- Power supplies:
 - Uninterruptible power supplies
 - AC/DC switch-mode power supplies
 - Lighting
- Synchronous rectification
- DC/DC converter
- Motor drive switch
- DC/AC inverter
- Battery management

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V_{DS}	40	V				
Gate-Source Voltage	V_{GS}	± 20					
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 25 °C	٥٦	320	A			
Continuous Diain Current (1) = 130 C)	T _C = 100 °C	Ū	225				
Pulsed Drain Current (t = 100 μs)	I _{DM}	1280	A				
Avalanche Current ^d	L = 0.1 mH	I _{AS}	I _{AS} 115				
Single Avalanche Energy ^a	L = 0.1 IIII1	E _{AS}	1230	mJ			
Maximum Power Dissipation ^a	T _C = 25 °C	PD	303 ^b	W			
Maximum Tower Dissipation -	T _C = 100 °C	l D	151 ^b	VV			
Operating Junction and Storage Temperature Ra	T _J , T _{stg}	-55 to +175	°C				

THERMAL RESISTANCE RATINGS							
PARAMETER	SYMBOL	LIMIT	UNIT				
Junction-to-Ambient (PCB Mount) ^c	t ≤ 10 s	R _{thJA}	15	°C/W			
Junction-to-Case (Drain)	Steady State	R _{thJC}	0.5	C/VV			

Notes

- a. Duty cycle \leq 1 %.
- b. See SOA curve for voltage derating.
- c. When mounted on 1" square PCB (FR4 material).
- d. Single pulse width limited by junction temperature TJ(MAX)=150°C.



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PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.5	-	3.5	V
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		V _{DS} = 40 V, V _{GS} = 0 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = 32 V, V_{GS} = 0 V, T_J = 85 °C	-	-	10	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	320	-	-	Α
Drain-Source On-State Resistance a	B	V _{GS} = 10 V, I _D = 30 A	-	0.8	0.98	mΩ
Dialit-Source Oit-State nesistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 30 \text{ A}$	-	1.5	2.2	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 30 A	-	108	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	7870	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	1380	-	
Reverse Transfer Capacitance	C _{rss}		-	855	-	
Total Gate Charge ^c	Qg		-	245	-	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 30 \text{ A}$	-	48	-	nC
Gate-Drain Charge ^c	Q _{gd}		-	52	-	
Gate Resistance	R_g	f = 1 MHz	-	2.8	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	38	-	
Rise Time ^c	t _r	V_{DD} = 20 V, I_D =30 A, R_g = 3 Ω	-	45	-	
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GEN} = 10 \text{ V}$	-	152	-	ns
Fall Time ^c	t _f		-	62	-	
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	320	Α
Pulsed Current (t = 100 μs)	I _{SM}		-	-	1280	Α
Forward Voltage ^a	V_{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1	V
Reverse Recovery Time	t _{rr}	L 20 A di/d+ E00 A/:-	-	49	-	ns
Reverse Recovery Charge	Q _{rr}	$I_F = 30 \text{ A}, \text{ di/dt} = 500 \text{ A/}\mu\text{s}$	-	175	_	nC

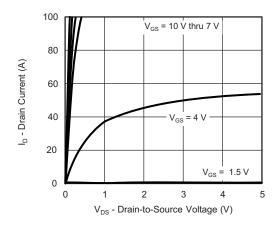
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

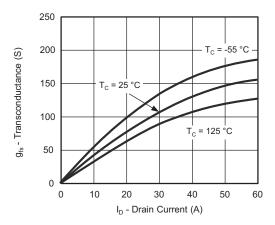
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



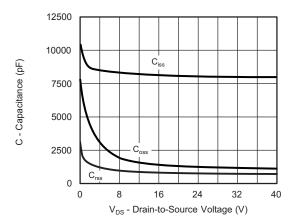
TYPICAL CHARACTERISTICS ($T_A = 25$ °C, unless otherwise noted)



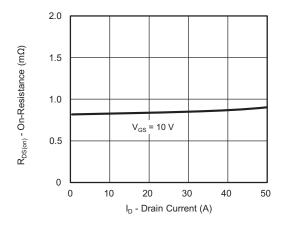
Output Characteristics



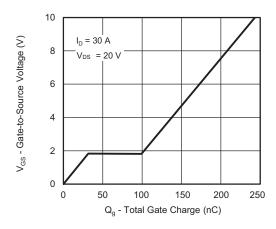
Transconductance



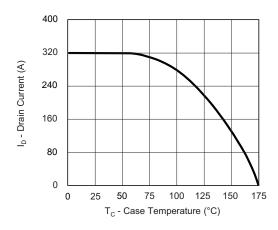
Capacitance



On-Resistance vs. Drain Current



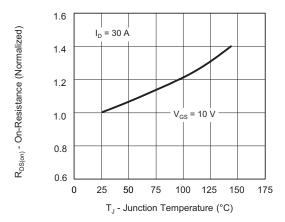
Gate Charge



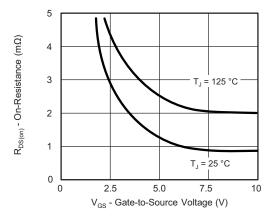
Current De-Rating



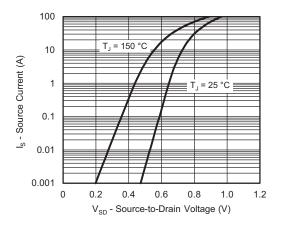
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



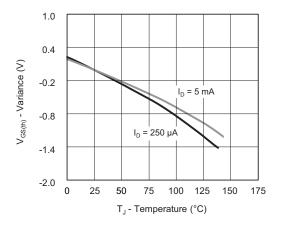
On-Resistance vs. Junction Temperature



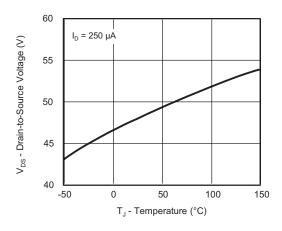
On-Resistance vs. Gate-to-Source Voltage



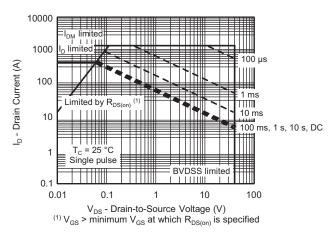
Source Drain Diode Forward Voltage



Threshold Voltage



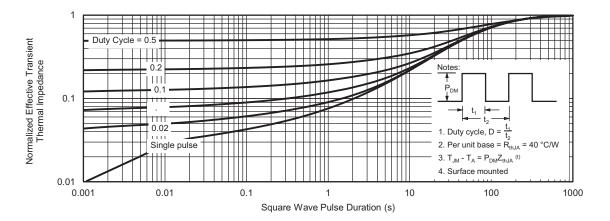
Drain Source Breakdown vs. Junction Temperature



Safe Operating Area



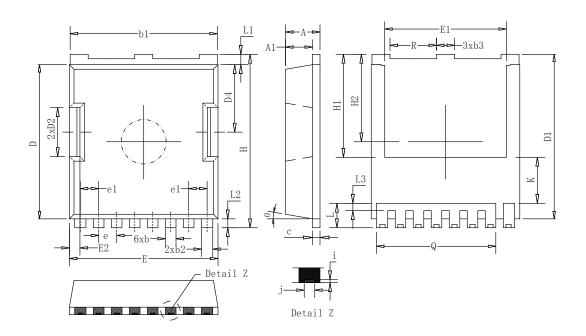
THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



TOLL PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
A	2.05	2.30	2.65	E2	0.40	0.70	0.90
A1	1.50	1.80	2.10	Н	11.30	11.70	12.10
b	0.50	0.70	0.90	H1	6.95 BSC		
b1	9.50	9.80	10.05	H2	5.90 BSC		
b2	0.50	0.75	1.00	i	0.10 REF		
b3	1.00	1.20	1.45	j	0.35 REF		
С	0.30	0.50	0.75	K	3.10 REF		
D	10.10	10.40	10.70	L	1.45 1.65 1.85		1.85
D1	10.80	11.10	11.40	L1	0.50	0.70	0.90
D2	3.10	3.30	3.50	L2	0.40	0.60	0.80
D4	4.35	4.55	4.80	L3	0.30	0.50	0.70
e	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC		R	2.80	3.10	3.35	
Е	9.65	9.90	10.15	θ	10°REF		
E1	7.80	8.10	8.50				





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